M Zafar Iqbal

List of Publications by Year
in descending order

31	324	1040056	888059
papers	citations	9	17
		h-index	g-index

32	32	32	173
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effects of irradiation and annealing on deep levels in rhodium-doped p-GaAs grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2011, 109, 113705.	2.5	0
2	Arsenic antisite defects in p-GaAs grown by metal-organic chemical-vapor deposition and the EL2 defect. Journal of Applied Physics, 2009, 106, .	2.5	9
3	4d transition-metal impurity rhodium in GaAs grown by metal-organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, 113708.	2.5	3
4	Electrical characterization of alpha radiation-induced defects in p-GaAs grown by metal-organic chemical-vapor deposition. Journal of Applied Physics, 2007, 101, 063701.	2.5	7
5	Osmium impurity-related deep levels in n-type GaAs. Journal of Applied Physics, 2005, 98, 083709.	2.5	1
6	Osmium related deep levels in n-type GaAs. Physica B: Condensed Matter, 2003, 340-342, 358-361.	2.7	0
7	Effect of ambient on photoluminescence from GaN grown by molecular-beam epitaxy. Journal of Electronic Materials, 2003, 32, 346-349.	2.2	20
8	Characteristics of deep levels associated with rhodium impurity in n-type GaAs. Journal of Applied Physics, 2003, 94, 3115-3120.	2.5	5
9	Optical properties of a silver-related defect in silicon. Physical Review B, 2003, 67, .	3.2	15
10	Rhodium-related deep levels in n-type MOCVD GaAs. Physica B: Condensed Matter, 2001, 308-310, 816-819.	2.7	3
11	Osmium Related Deep Levels in Indium Phosphide. Physica Status Solidi A, 1999, 171, 521-537.	1.7	2
12	Ruthenium: A superior compensator of InP. Applied Physics Letters, 1998, 73, 3878-3880.	3.3	32
13	Interaction of iron with transition metals and alpha radiation in thermally quenched p-silicon. Semiconductor Science and Technology, 1997, 12, 1100-1105.	2.0	4
14	Bleaching of the interstitial iron donor in silicon by transition metal impurities. Semiconductor Science and Technology, 1996, 11, L129-L132.	2.0	5
15	Study of deep levels in alphaâ€irradiated silverâ€dopedpâ€type silicon. Journal of Applied Physics, 1995, 77, 5050-5059.	2.5	6
16	Study of the alpha irradiation and thermal annealing of goldâ€dopednâ€type silicon. Journal of Applied Physics, 1995, 77, 5572-5579.	2.5	7
17	Effects of annealing and Î± irradiation on deep levels in silverâ€dopednâ€type silicon. Journal of Applied Physics, 1995, 77, 3315-3322.	2.5	8
18	Atmospheric-pressure synthesis of the YBa2Cu4O8superconductor using Cu2(CN)2. Superconductor Science and Technology, 1994, 7, 563-568.	3.5	1

#	Article	IF	Citations
19	Deep levels in alphaâ€irradiated platinum dopednâ€type silicon. Journal of Applied Physics, 1994, 76, 2553-2555.	2.5	3
20	Interaction of Î±â€radiation induced defects with Pdâ€related deep levels in silicon. Journal of Applied Physics, 1994, 75, 7737-7744.	2.5	3
21	Mechanism of decomposition of cuprous cyanide. Infrared and thermal evidence. Chemistry of Materials, 1993, 5, 1283-1286.	6.7	26
22	Simple method for direct synthesis of YBa2Cu4O8at atmospheric oxygen pressure. Applied Physics Letters, 1993, 63, 257-259.	3.3	38
23	Characterization of deep levels introduced by alpha radiation innâ€type silicon. Journal of Applied Physics, 1993, 73, 3698-3708.	2.5	30
24	Study of alphaâ€radiationâ€induced deep levels inpâ€type silicon. Journal of Applied Physics, 1993, 73, 4240-4247.	2.5	27
25	Role of boat material in the synthesis of 123 superconductor from copper cyanide. Journal of Materials Science Letters, 1993, 12, 607-608.	0.5	2
26	Y-Ba-Cu (1-2-3) superconductor starting with copper cyanide. Journal of Materials Science Letters, 1991, 10, 1182-1183.	0.5	7
27	Electron capture cross sections of the platinum donor level in silicon. Semiconductor Science and Technology, 1990, 5, 1133-1135.	2.0	2
28	Role of the midâ€gap level as the dominant recombination center in platinum doped silicon. Journal of Applied Physics, 1990, 67, 1130-1132.	2.5	24
29	Î±â€radiationâ€induced deep levels in lowâ€dopednâ€type silicon. Journal of Applied Physics, 1990, 68, 887-889.	2.5	3
30	Characterization of silverâ€related deep levels in silicon. Journal of Applied Physics, 1987, 62, 2853-2857.	2.5	28
31	?0.75 eV killer centre? in red-emitting GaP LEDs. Applied Physics A: Solids and Surfaces, 1983, 32, 223-224.	1.4	2